600V, 15A, Trench FS II Fast IGBT

General Description:

Using QIAOXIN's proprietary trench design and advanced FS (Field Stop) second generation technology, the 600V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

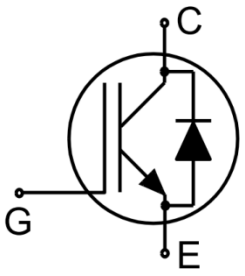
Features

Trench FSII Technology offering

- Very low $V_{CE\ (sat)}$
- High speed switching
- Positive temperature coefficient in $V_{CE\ (sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Air Condition
- Inverters
- Motor drives



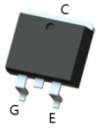
Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking
VCRR15TD60BD	TO-263	
VCRR15TD60B	TO-220	
VCRR15TD60BF	TO-220F	

TO-220F

TO-220



TO-263

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	TO-220/TO-263	TO-220F	Units
V_{CES}	Collector-Emitter Voltage	600		V
V_{GES}	Gate- Emitter Voltage	±30		V
I_C	Collector Current	30	30*	A
	Collector Current @T_C = 100 °C	15	15*	A
I_{Cplus}	Pulsed Collector Current，t_p limited by T_{jmax}	45	45	A
-	turn off safe operating area，VCE=600V，Tj=150℃	45	45	A
I_F	Diode Continuous Forward Current @T_C = 100 °C	15	15*	A
I_{FM}	Diode Maximum Forward Current	45	45	A
P_D	Power Dissipation @ T_C = 25°C	105	34	W
	Power Dissipation @T_C = 100 °C	42	13.6	W
T_J,T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150		℃
T_L	Maximum Temperature for Soldering	260		℃
t_{sc}	Short circuit withstand time V_{GE}=15.0V, V_{CC}≤400V, Allowed number of short circuits<1000Time between short circuits:≥1.0s,T_j≤150℃	3		us

Thermal Characteristic

Symbol	Parameter	TO-220/TO-263	TO-220F	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	1.19	3.67	℃/W
$R_{\theta JC}$	Thermal Resistance, Junction to case for Diode	2.12	3.97	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62	78	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Symbol	Parameter	Test Conditions		Rating			Units
				Min.	Typ.	Max.	
STATIC Characteristics							
$V_{(BR)CES}$	Collector-EmitterBreakdown Voltage	V_{GE}=0V,I_{CE}=1mA		600	--	--	V
I_{CES}	Collector-Emitter Leakage Current	V_{GE} =0V,V_{CE}=600V		--	--	4	uA
$I_{GES(F)}$	Gate to Emitter Forward Leakage	V_{GE}=+30V,V_{CE}=0V		--	--	100	nA
$I_{GES(R)}$	Gate to Source Reverse Leakage	V_{GE}=-30V,V_{CE} =0V		--	--	100	nA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=15A	Tj=25℃	--	1.7	1.9	V
		V_{GE}=15V	Tj=100℃	--	1.9	--	V
$V_{GE(th)}$	Gate Threshold Voltage	I_C=1mA,V_{CE}=V_{GE}		4.0	--	6.0	V
Dynamic Characteristics							
C_{ies}	Input Capacitance	V_{CE}=25V,V_{GE}=0V, f=1MHz		--	1635	--	pF
C_{oes}	Output Capacitance			--	50	--	
C_{res}	Reverse Transfer Capacitance			--	30	--	
Q_g	Total Gate Charge	V_{CC}=480V, I_C=15A V_{GE}=15V		--	63	--	nC
Q_{ge}	Gate to Emitter Charge			--	15	--	nC
Q_{gc}	Gate to Collector Charge			--	26	--	nC
$I_{C(SC)}$	Short circuit collector current Max.1000 short circuits Time between short circuits: ⩾1.0s	V_{GE}=15V,V_{CC}⩽400V, t_{SC}⩽3us,Tj⩽150℃		--	82	--	A
Switching Characteristics							
$t_{d(ON)}$	Turn-on Delay Time	V_{CE}=400V,I_C=10A V_{GE}=0/15V, R_g=5Ω Inductive Load		--	16	--	ns
t_r	Rise Time			--	12	--	
$t_{d(OFF)}$	Turn-Off Delay Time			--	124	--	
t_f	Fall Time			--	12	--	
E_{on}	Turn-On Switching Loss			--	0.25	--	mJ
E_{off}	Turn-Off Switching Loss			--	0.12	--	
E_{ts}	Total Switching Loss			--	0.37	--	

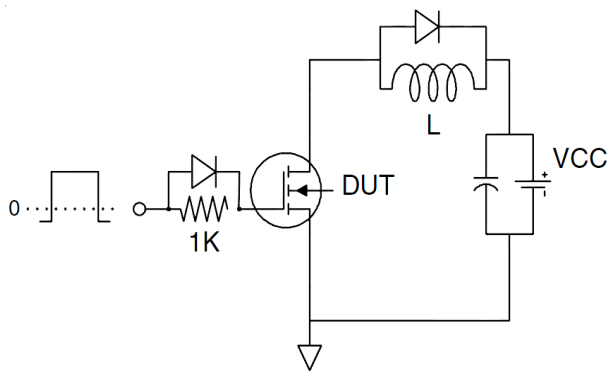
Electrical Characteristics of the Diode(T_C= 25℃ unless otherwise specified)：

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{FM}	Diode Forward Voltage	I_F=15A	--	1.5	1.7	V
T_{rr}	Reverse Recovery Time	Vcc=400V, I_F=15A, di/dt=200A/uS	--	170	--	ns
I_{RRM}	Diode Peak Reverse Recovery Current		--	6.5	--	A
Q_{rr}	Reverse Recovery Charge		--	0.7	--	uC
Pulse width t_{tp}≤380μs,δ≤2%						

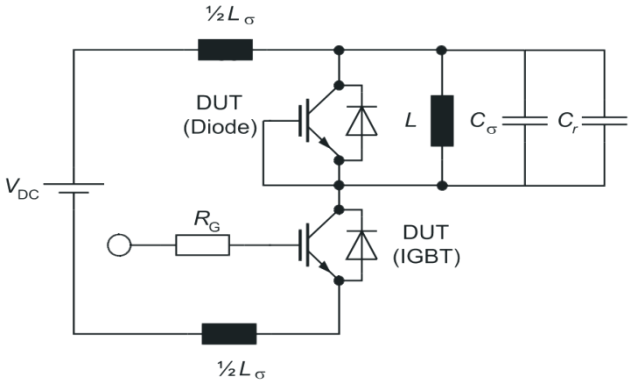
* TO-220F Ic Follow TO-220/TO-263.

Test Circuit

1) Gate Charge Test Circuit

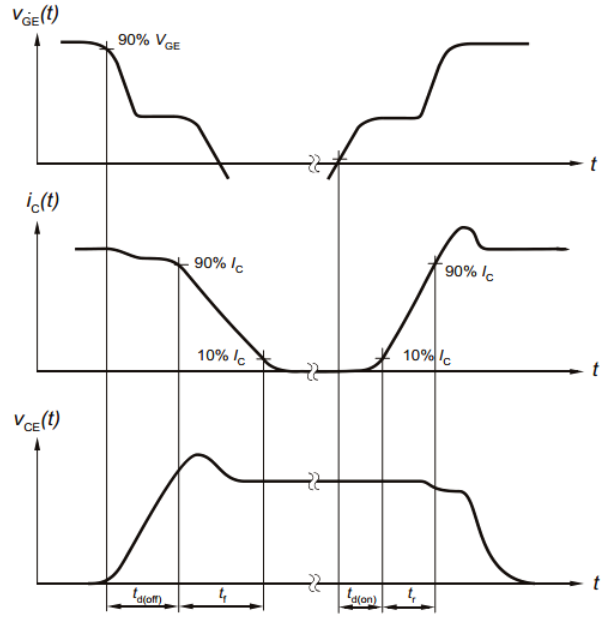


2) Switch Time Test Circuit

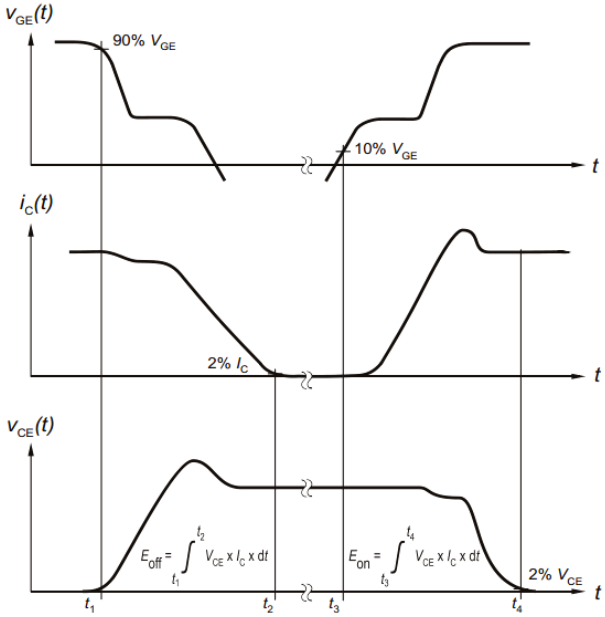


Switching characteristics

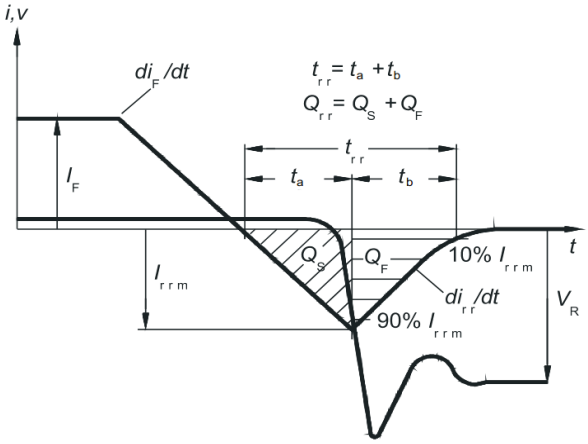
1) definition of switching times



2) definition of switching losses



3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

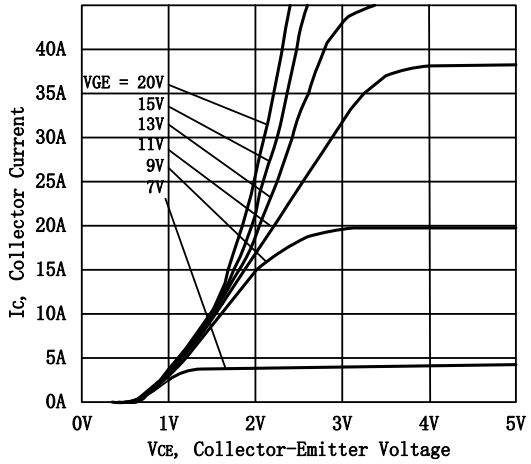


Figure 2 Transfer Characteristics

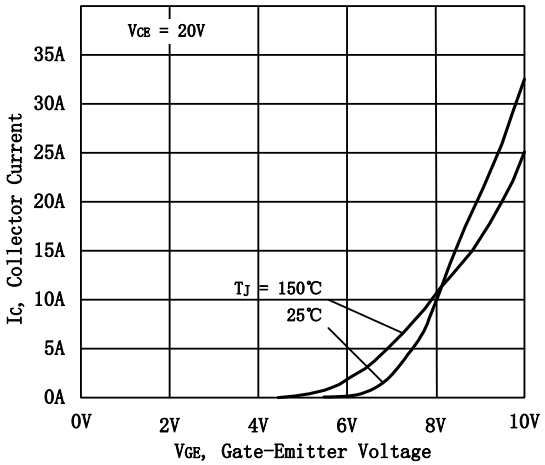


Figure 3 V_{CEsat} vs. Case Temperature

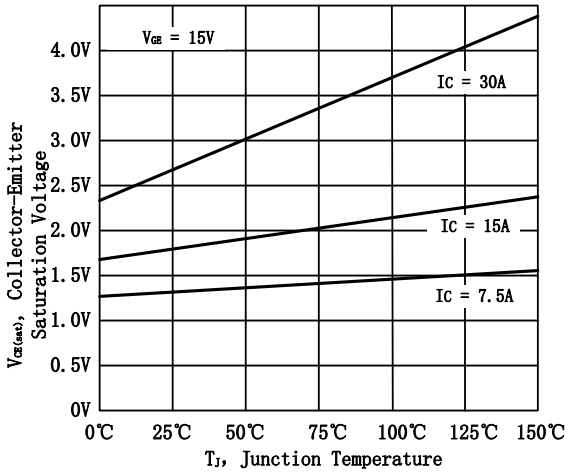


Figure 4 Saturation Voltage vs. VGE

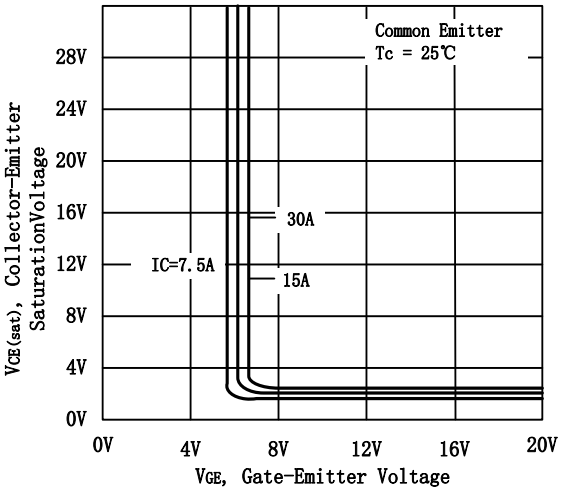


Figure 5 Capacitance Characteristics

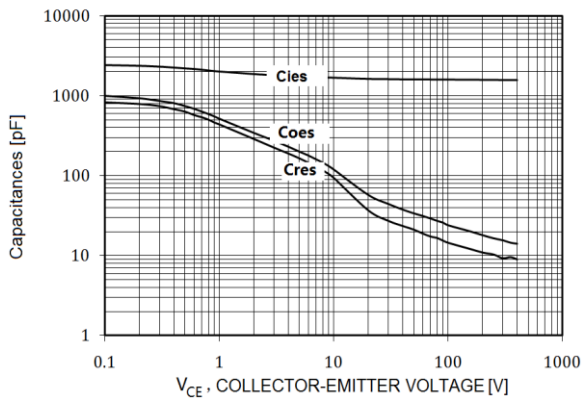


Figure 6 Gate charge waveform

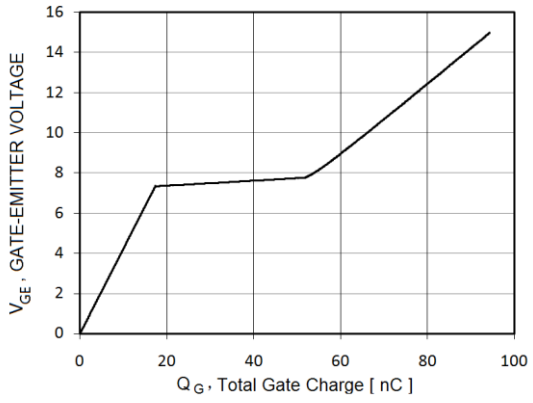


Figure 7 Gate-emitter Threshold Voltage as a Function of Junction Temperature

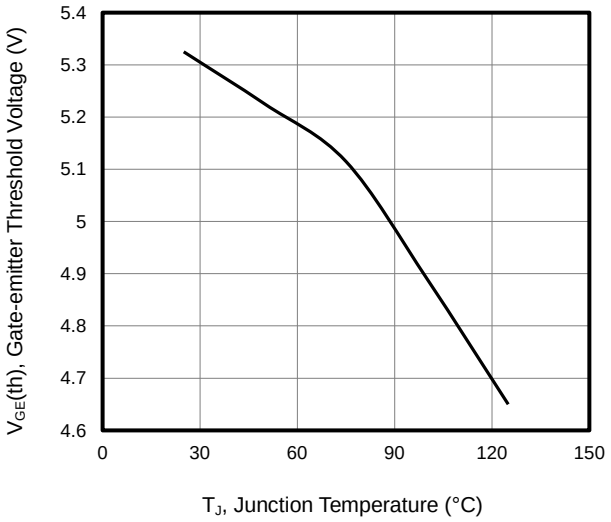


Figure 8 Typical Switching Times as a Function of Gate Resistor

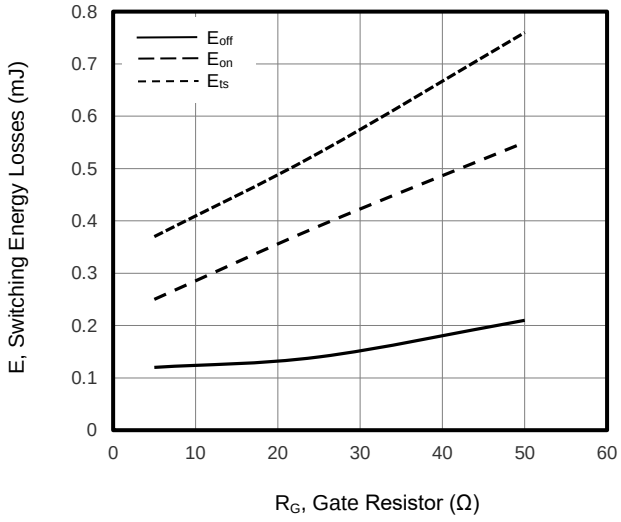


Figure 9 Typical Switching Times as a Function of Junction Temperature

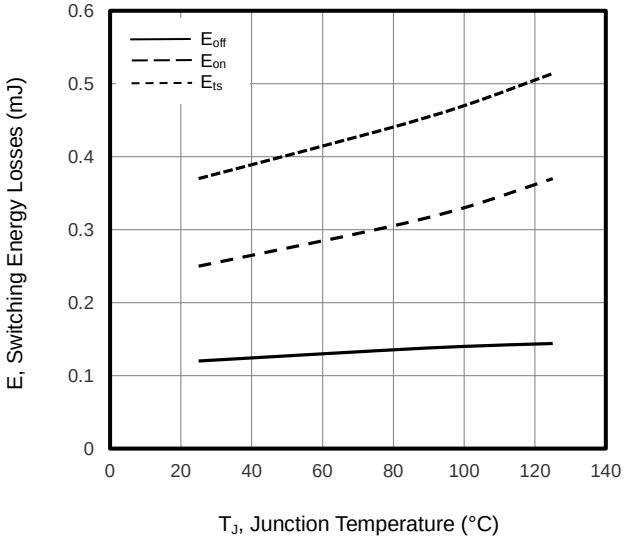


Figure10 Power Dissipation as a Function of Case Temperature

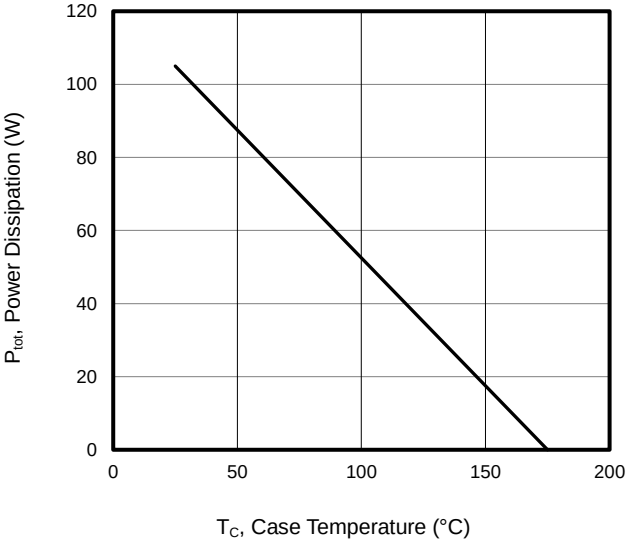


Figure 11 Reverse Bias SOA

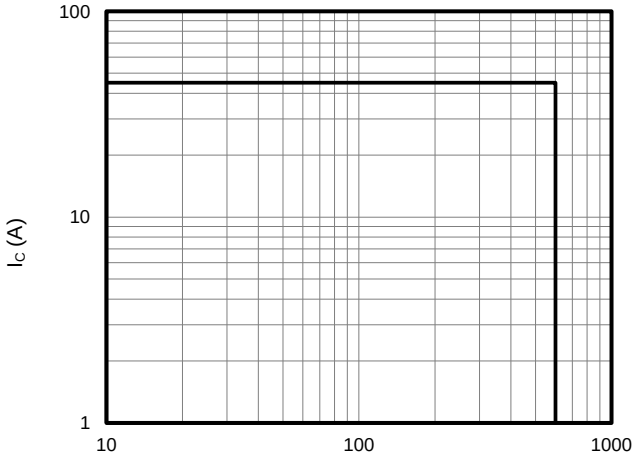
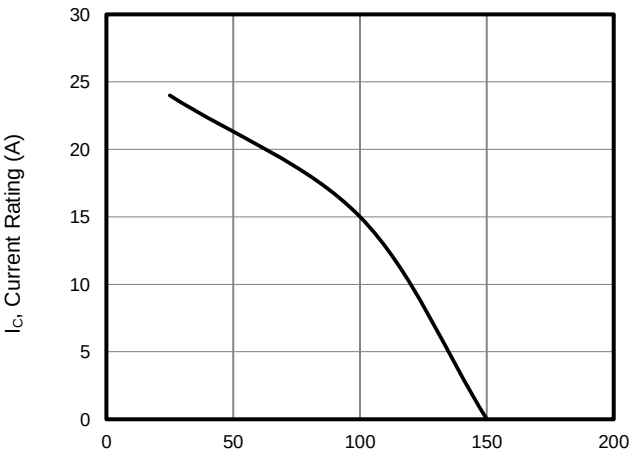


Figure 12 Current De-rating



Typical Electrical and Thermal Characteristics（continued）

Figure 13 Forward Characteristics

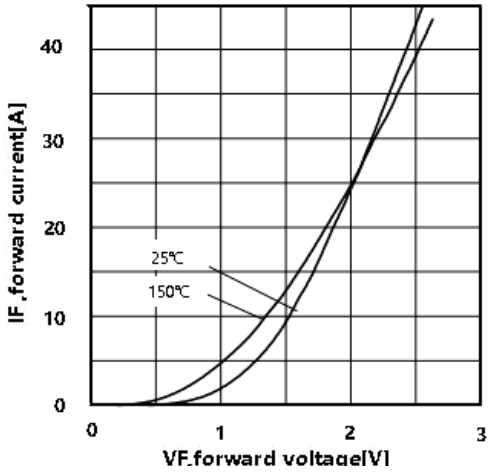


Figure 14 V_F vs. temperature

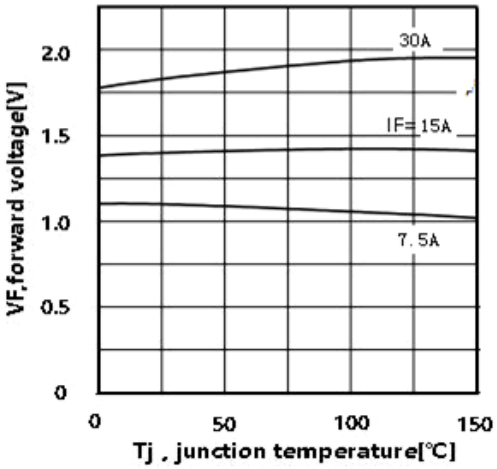


Figure 15 Transient Thermal Impedance of IGBT for TO-220F

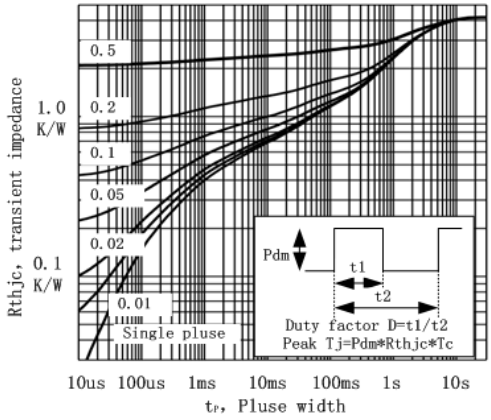
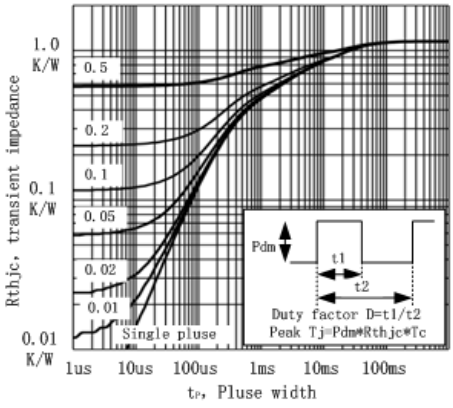
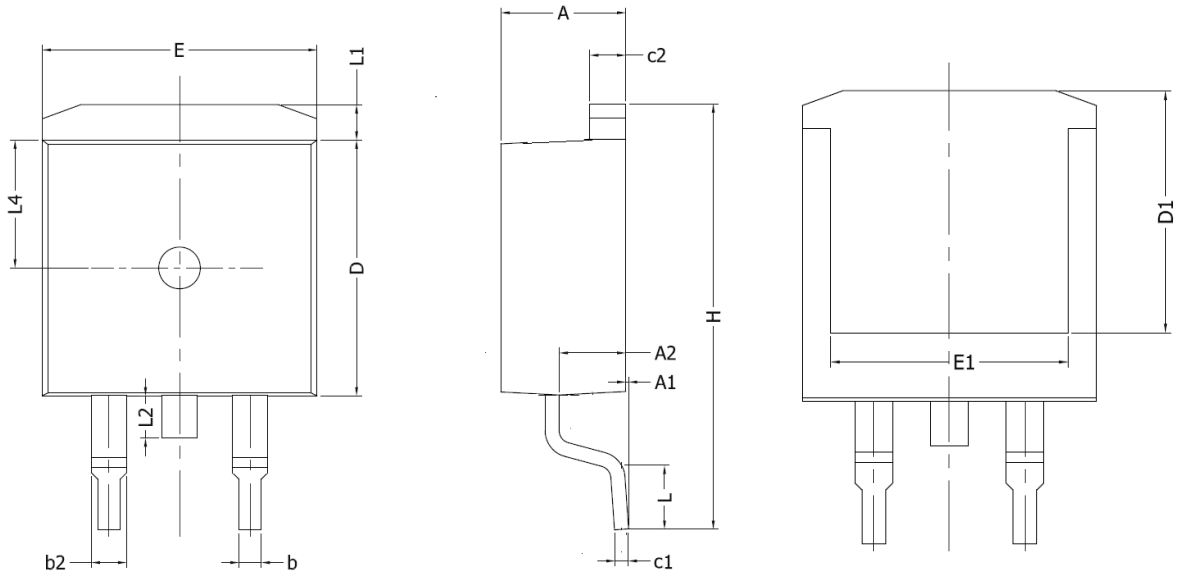


Figure 16 Transient Thermal Impedance of IGBT for TO-220,TO-263

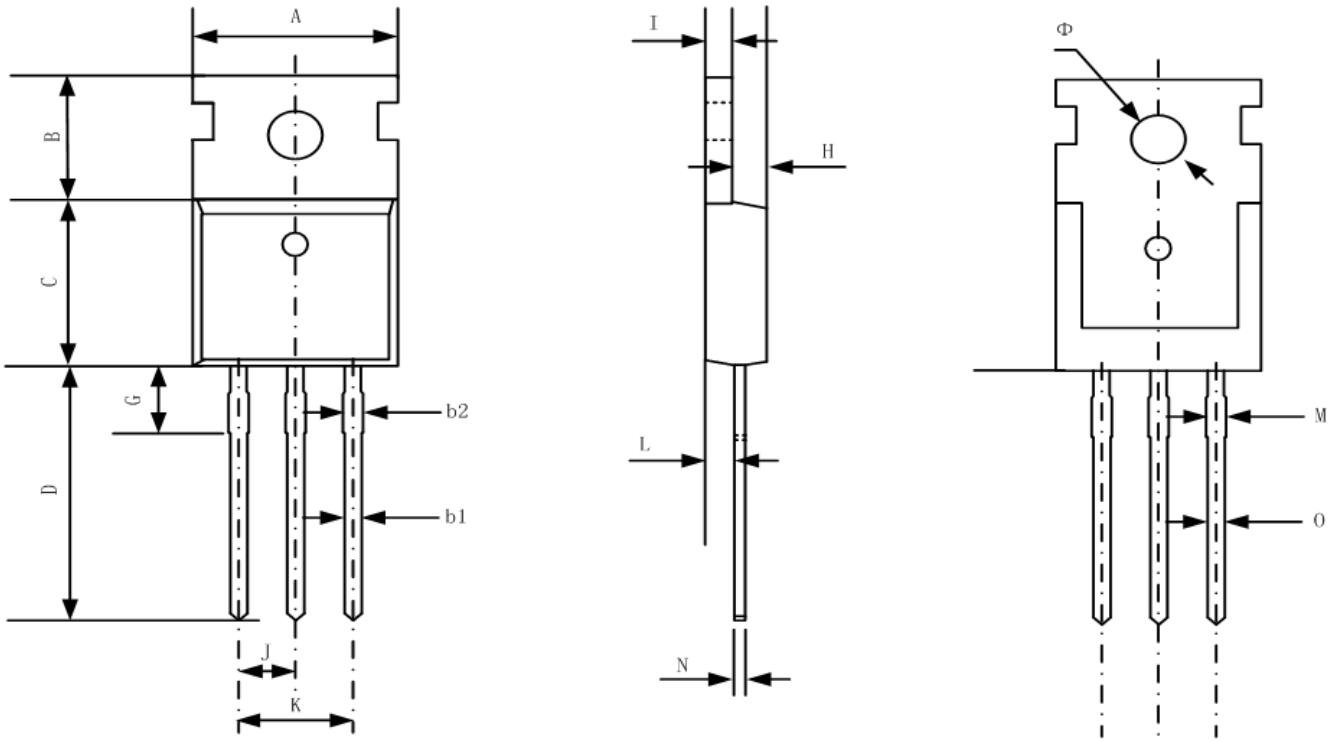


TO-263-3L Package Information



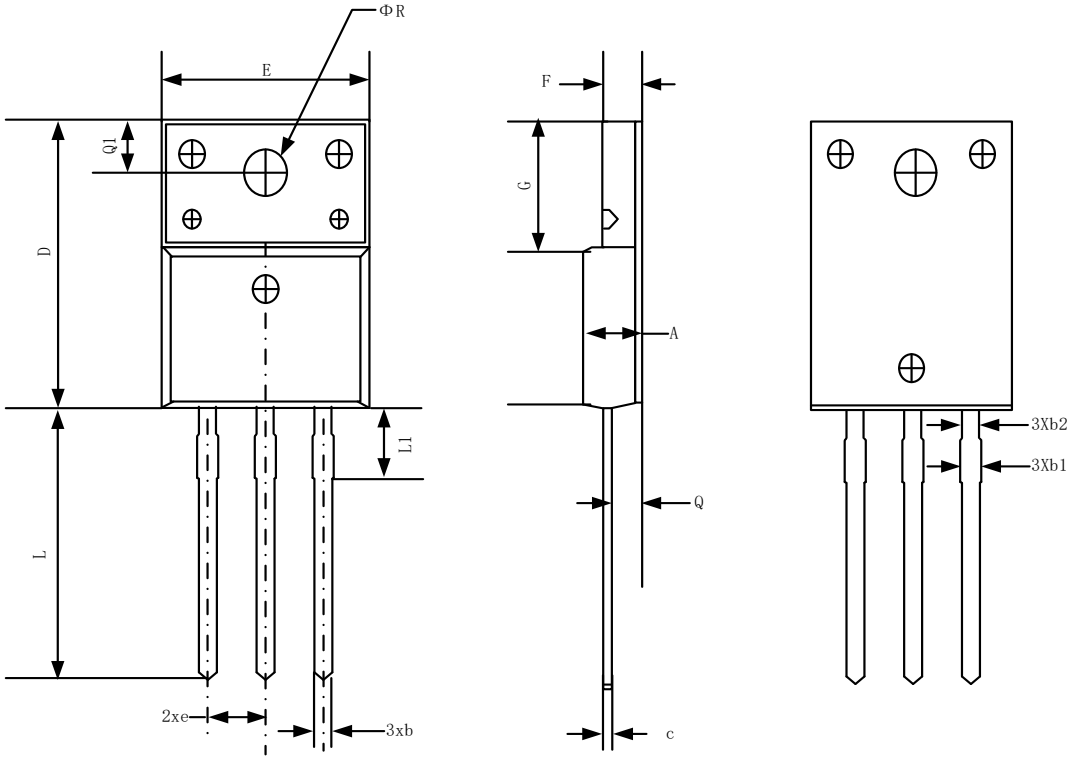
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.17	0.18
A1	0.00	0.25	0.00	0.01
A2	2.20	2.60	0.09	0.10
b	0.76	0.89	0.03	0.04
b2	1.23	1.37	0.05	0.05
C	0.47	0.60	0.02	0.02
c1	0.46	0.56	0.02	0.02
c2	1.25	1.35	0.05	0.05
D	0.91	0.93	0.04	0.04
D1	8.00	-	0.31	-
E	9.80	10.00	0.39	0.39
E1	7.80	-	0.31	-
e	2.54BSC		0.10BSC	
H	14.90	15.70	0.59	0.62
L	2.00	2.60	0.08	0.10
L1	1.17	1.40	0.05	0.06
L2	-	1.75	-	0.07
L4	4.60REF		0.18REF	

TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	9.70	10.20	0.38	0.40
B	6.30	6.70	0.25	0.26
C	9.00	9.47	0.35	0.37
D	12.78	13.38	0.50	0.53
G	2.65 REF		0.104 REF	
H	3.00	3.40	0.12	0.13
I	1.25	1.40	0.05	0.06
J	2.40	2.70	0.09	0.11
K	5.00	5.15	0.20	0.20
L	2.20	2.60	0.09	0.10
M	1.25	1.45	0.05	0.06
N	0.45	0.60	0.02	0.02
O	0.70	0.90	0.03	0.04
Φ	3.6 REF		0.142 REF	

TO-220F Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.50	4.83	0.18	0.19
b	0.70	0.91	0.03	0.04
b1	1.20	1.47	0.05	0.06
b2	1.10	1.38	0.04	0.05
c	0.45	0.63	0.02	0.02
D	15.67	16.07	0.62	0.63
e	2.54 BSC		0.10 BSC	
E	9.96	10.36	0.39	0.41
F	2.34	2.74	0.09	0.11
G	6.48	6.90	0.26	0.27
L	12.68	13.30	0.50	0.52
L1	3.13	3.50	0.12	0.14
Q	2.56	2.93	0.10	0.12
Q1	3.20	3.40	0.13	0.13
ΦR	3.08	3.28	0.12	0.13

Attention

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